



N-Channel NexFET™ Power MOSFETs

Check for Samples: CSD16407Q5

FEATURES

- Ultralow Qg and Qgd
- Low Thermal Resistance
- Avalanche Rated
- SON 5-mm × 6-mm Plastic Package

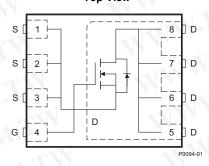
APPLICATIONS

- Point-of-Load Synchronous Buck Converter for Applications in Networking, Telecom and Computing Systems
- Optimized for Synchronous FET Applications

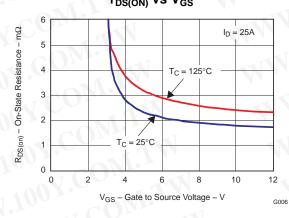
DESCRIPTION

The NexFET™ power MOSFET has been designed to minimize losses in power conversion applications.





r_{DS(ON)} vs V_{GS}



PRODUCT SUMMARY

V _{DS}	Drain-to0source voltage	25	$I(0)_{\tilde{I}}$	V
Q_g	Gate charge, total (4.5 V)	13.3		nC
Q_{gd}	Gate charge, gate-to-drain	3.5	40	nC
	Davis 4	V _{GS} = 4.5 V	2.5	mΩ
R _{DS(on)}	Drain-to-source on-resistance	V _{GS} = 10 V	1.8	mΩ
V _{GS(th)}	Threshold voltage	1.6	7 C	V

ORDERING INFORMATION

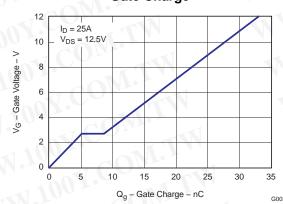
Device	Package	Media	Qty	Ship
CSD16407Q5	SON 5 x 6 plastic package	13-inch reel	2500	Tape and reel

ABSOLUTE MAXIMUM RATINGS

T _A = 2	5°C unless otherwise stated	VALUE	UNIT
V _{DS}	Drain-to-source voltage	25	V
V_{GS}	Gate-to-source voltage	+16 / -12	V
	Continuous drain current, T _C = 25°C	100	Α
I _D	Continuous drain current ⁽¹⁾	31	Α
I _{DM}	Pulsed drain current, T _A = 25°C ⁽²⁾	200	A
P_{D}	Power dissipation ⁽¹⁾	3.1	W
T _J , T _{STG}	Operating junction and storage temperature range	-55 to 150	°C
E _{AS}	Avalanche energy, single pulse $I_D = 66A$, $L = 0.1$ mH, $R_G = 25$ Ω	218	mJ

- (1) $R_{\theta,JA} = 40^{\circ}\text{C/W}$ on 1 in² (6.45 cm²) Cu [2 oz. (0.071 mm thick)] on 0.060-inch (1.52-mm) thick FR4 PCB.
- (2) Pulse duration ≤300 μs, duty cycle ≤2%

Gate Charge



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ELECTRICAL CHARACTERISTICS

 $(T_{\Delta} = 25^{\circ}C \text{ unless otherwise stated})$

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Static Ch	naracteristics		0			
BV _{DSS}	Drain-to-source voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	25	,		V
I _{DSS}	Drain-to-source leakage current	V _{GS} = 0 V, V _{DS} = 20 V	4	001	1	μΑ
I _{GSS}	Gate-to-source leakage current	$V_{DS} = 0 \text{ V}, V_{GS} = 16 \text{ V to } -12 \text{ V}$		TO O	100	nA
V _{GS(th)}	Gate-to-source threshold voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1.3	1.6	1.9	٧
-	Droin to course on registance	$V_{GS} = 4.5 \text{ V}, I_D = 25 \text{ A}$		2.5	3.3	$m\Omega$
r _{DS(on)}	Drain-to-source on-resistance	V _{GS} = 10 V, I _D = 25 A		1.8	2.4	mΩ
g _{fs}	Transconductance	V _{DS} = 15 V, I _D = 25 A		111	O >	S
Dynamic	: Characteristics	7 CONTENT			-01	
C _{ISS}	Input capacitance	7.		2040	2660	pF
Coss	Output capacitance	V _{GS} = 0 V, V _{DS} = 12.5 V, f = 1 MHz	-4111	1600	2080	pF
C _{RSS}	Reverse transfer capacitance	TI		115	160	pF
R _g	Series gate resistance	COMP	-11	1.2	2.4	Ω
Qg	Gate charge total (4.5 V)			13.3	18	nC
Q_{gd}	Gate charge, gate-to-drain	V 40.5 V 1 25.A		3.5	1.1	nC
Q _{gs}	Gate charge, gate-to-source	V _{DS} = 12.5 V, I _D = 25 A		5.3	- 10	nC
Qg(th)	Gate charge at Vth	In		3.1	(N.1)	nC
Q _{OSS}	Output charge	V _{DS} = 13.5 V, V _{GS} = 0 V	1	33		nC
t _{d(on)}	Turnon delay time	100		11.9		ns
t _r	Rise time	V _{DS} = 12.5 V, V _{GS} = 4.5 V, I _D = 25 A		18.4		ns
t _{d(off)}	Turnoff delay time	$R_G = 2 \Omega$		16		ns
t_f	Fall time	M. CO.		9		ns
Diode Ch	naracteristics	-1100 h			-13	
V _{SD}	Diode forward voltage	I _S = 25 A, V _{GS} = 0 V		0.8	1	V
Q _{rr}	Reverse recovery charge	$V_{DD} = 13.5 \text{ V}, I_F = 25 \text{ A}, di/dt = 300 \text{ A}/\mu\text{s}$		41		nC
t _{rr}	Reverse recovery time	$V_{DD} = 13.5 \text{ V}, I_F = 25 \text{ A}, di/dt = 300 \text{ A/}\mu\text{s}$	KT	34		ns

THERMAL CHARACTERISTICS

(T_A = 25°C unless otherwise stated)

	PARAMETER	MIN	TYP	MAX	UNIT
R	_{BJC} Thermal resistance, junction-to-case ⁽¹⁾			1.1	°C/W
R	_{0JA} Thermal resistance, junction-to-ambient ⁽¹⁾ (2)	1	ľ	51	°C/W

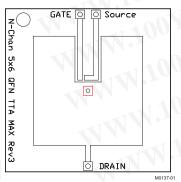
⁽¹⁾ R_{θJC} is determined with the device mounted on a 1-inch (2.54-cm) square 2-oz (0.071-mm thick). Cu pad on a 1.5-inch (3.81-cn) x 1.5-inch (3.81-cm) x 0.060-inch (1.52-mm) thick FR4 board. R_{θJC} is specified by design, whereas R_{θJA} is determined by the user's board design.

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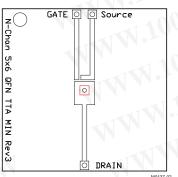
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⁽²⁾ Device mounted on FR4 material with 1 inch² (6.45 cm²) of 2-oz. (0.071-mm thick) Cu.





Max $R_{\theta JA} = 50^{\circ}\text{C/W}$ when mounted on 1 inch² (6.45 cm²) of 2-oz. (0.071-mm thick) Cu.



Max $R_{\theta JA} = 121^{\circ} C/W$ when mounted on minimum pad area of 2-oz. (0.071-mm thick) Cu.

TYPICAL MOSFET CHARACTERISTICS

(T_A = 25°C unless otherwise stated)

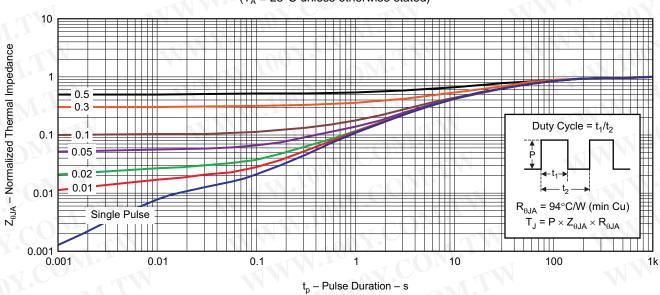


Figure 1. Transient Thermal Impedance

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TYPICAL MOSFET CHARACTERISTICS (continued)

$(T_A = 25^{\circ}C \text{ unless otherwise stated})$

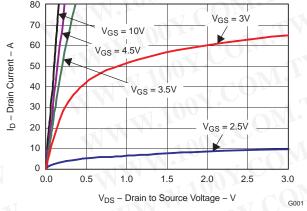


Figure 2. Saturation Characteristics

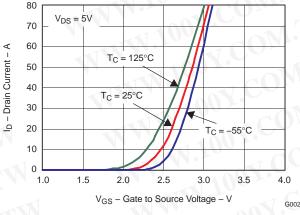


Figure 3. Transfer Characteristics

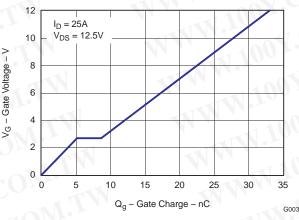


Figure 4. Gate Charge

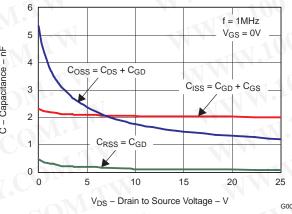


Figure 5. Capacitance

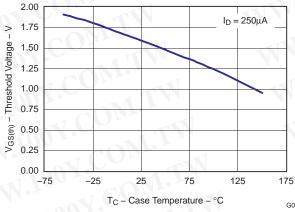


Figure 6. Threshold Voltage vs. Temperature

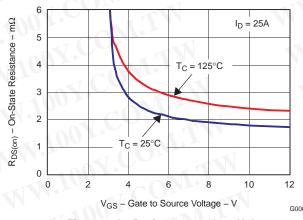


Figure 7. On Resistance vs. Gate Voltage



TYPICAL MOSFET CHARACTERISTICS (continued)

(T_A = 25°C unless otherwise stated)

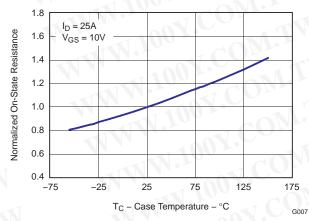


Figure 8. On Resistance vs. Temperature

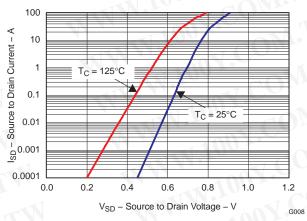


Figure 9. Typical Diode Forward Voltage

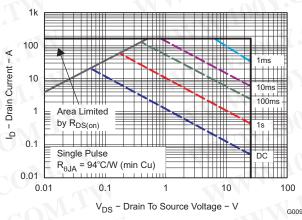


Figure 10. Maximum Safe Operating Area

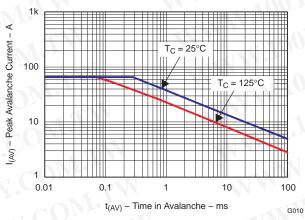


Figure 11. Single Pulse Unclamped Inductive Switching

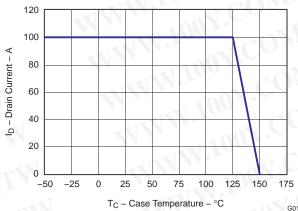
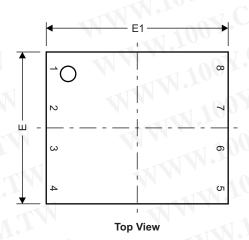


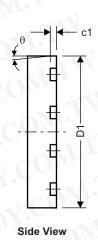
Figure 12. Maximum Drain Current vs. Temperature

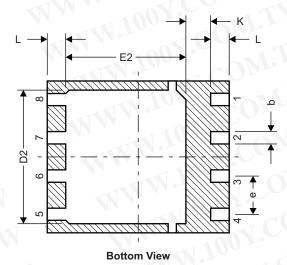


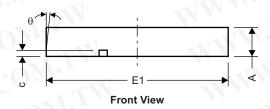
MECHANICAL DATA

Q5 Package Dimensions





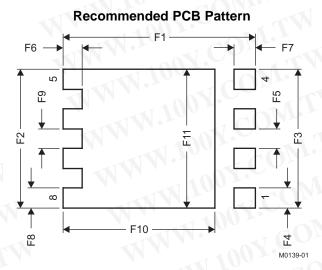




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DINA.	MILLIN	METERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	0.950	1.050	0.037	0.039
b	0.360	0.460	0.014	0.018
С	0.150	0.250	0.006	0.010
c1	0.150	0.250	0.006	0.010
D1	4.900	5.100	0.193	0.201
D2	4.320	4.520	0.170	0.178
E	4.900	5.100	0.193	0.201
E1	5.900	6.100	0.232	0.240
E2	3.920	4.12	0.154	0.162
е	1.27	TYP	0.	050
L	0.510	0.710	0.020	0.028
θ	0.00	- xx 1 3	- 40	11
К	0.760	4	0.030	-11

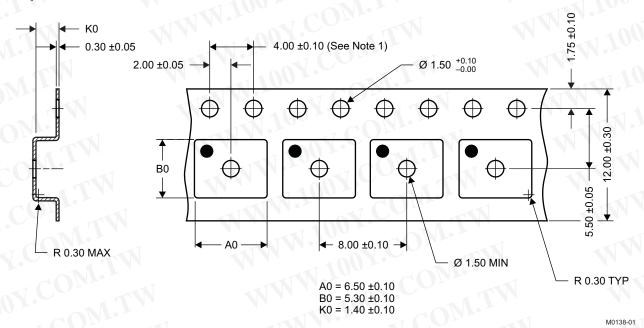




DIM	MILLIM	ETERS	INCI	HES
DIM	MIN	MAX	MIN	MAX
F1	6.205	6.305	0.2440	0.248
F2	4.460	4.560	0.1760	0.180
F3	4.460	4.560	0.1760	0.180
F4	0.650	0.700	0.0260	0.028
F5	0.620	0.670	0.0240	0.026
F6	0.630	0.680	0.0250	0.027
F7	0.70	0.800	0.0380	0.031
F8	0.650	0.700	0.0260	0.028
F9	0.620	0.670	0.0240	0.026
F10	4.900	5.000	0.1930	0.197
F11	4.460	4.560	0.1760	0.180

For recommended circuit layout for PCB designs, see application note SLPA005 – Reducing Ringing Through PCB Layout Techniques.

Q5 Tape and Reel Information



Notes:

- 1. 10 sprocket hole pitch cumulative tolerance ±0.2
- 2. Camber not to exceed 1 mm IN 100 mm, noncumulative over 250 mm
- 3. Material:black static dissipative polystyrene
- 4. All dimensions are in mm (unless otherwise specified)
- 5. Thickness: 0.30 ±0.05 mm
- 6. MSL1 260°C (IR and Convection) PbF Reflow Compatible



REVISION HISTORY

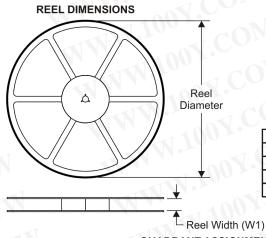
CI	Changes from Revision Original (August 2009) to Revision A	Page
•	Deleted environmental bullets from features list	
•	Deleted package marking at end of data sheet	

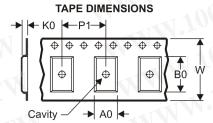
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PACKAGE MATERIALS INFORMATION

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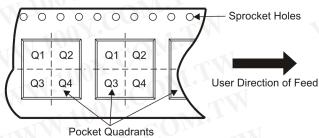
TAPE AND REEL INFORMATION





		Dimension designed to accommodate the component width
		Dimension designed to accommodate the component length
.\	K0	Dimension designed to accommodate the component thickness
	W	Overall width of the carrier tape
	P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



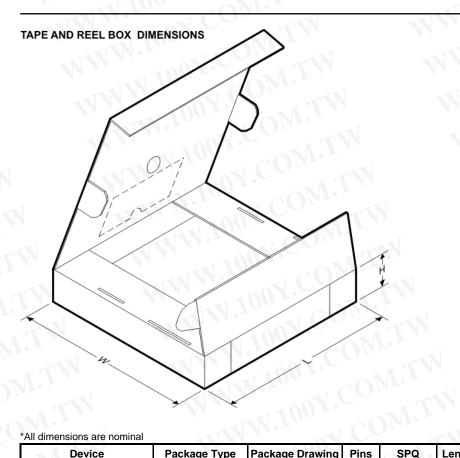
*All dimensions are nominal

1	Device	Package Type	Package Drawing			Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
	CSD16407Q5	SON	DQH	8	2500	330.0	12.8	6.5	5.3	1.4	8.0	12.0	Q1

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dimensions are nominal		•	N 100Y.						
	dimensions are nomina Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)	

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